

L Number	Hits	Search Text	DB	Time stamp
-	1	("20020037462").PN.	USPAT; US_PGPUB	2003/01/21 11:31
-	2	((("6051349") or ("5968691"))).PN.	USPAT; US_PGPUB	2003/03/31 15:25
-	28	((("6541170") or ("6457882") or ("6431769") or ("6281962") or ("6266125") or ("6221787") or ("5845170") or ("5939130") or ("6543080") or ("6492271") or ("5879854") or ("6185472") or ("6001461") or ("5817174") or ("6436723") or ("6431185") or ("6010797") or ("6118280") or ("5485549") or ("6398429") or ("5908657") or ("6444029") or ("6033475") or ("6023084") or ("5831300") or ("5933726") or ("5933724") or ("5804479") or ("5937290")).PN.	USPAT; US_PGPUB	2003/04/01 17:47
-	13	((("6541170") or ("6457882") or ("6431769") or ("6281962") or ("6266125") or ("6221787") or ("5845170") or ("5939130") or ("6543080") or ("6492271") or ("5879854") or ("6185472") or ("6001461") or ("5817174") or ("6436723") or ("6431185") or ("6010797") or ("6118280") or ("5485549") or ("6398429") or ("5908657") or ("6444029") or ("6033475") or ("6023084") or ("5831300") or ("5933726") or ("5933724") or ("5804479") or ("5937290")).PN.) and ((spin\$4 or rotat\$3 or centrifug\$3) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)	USPAT; US_PGPUB	2003/04/01 18:32
-	1695	(430/22,30,311,313,322,330.ccls. and ((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2003/04/01 18:34
-	1589	(430/22,30,311,313,322,330.ccls. and ((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2003/09/27 14:42
-	603	(430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2003/09/27 14:58
-	40	(430/30.ccls. not (430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((accelerat\$4 or speed\$3 or rotat\$4 or spin\$4) same (resist or photoresist or photosens\$5 or photopolymer\$7) same (nozzle or pipe or spread\$3 or dispense\$3 or flow\$3)))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2003/04/10 19:43

	0	(430/30.ccls. not (430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((accelerat\$4 or speed\$3 or rotat\$4 or spin\$4) same (resist or photoresist or photosens\$5 or photopolymer\$7)) same (nozzle or pipe or spread\$3 or dispense\$3 or flow\$3)) not (430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((accelerat\$4 or speed\$3 or rotat\$4 or spin\$4) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/12 12:54
	5	427/8-10 not (430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) not (430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 15:12
	66	(substrate or wafer) near3 (defect or fault) same (nozzle or pipe or spread\$3 or flow\$3 or dispense\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 15:12
	1	"5489337".PN.	USPAT; US-PGPUB	2003/04/11 09:53
	1	"5912054".PN.	USPAT; US-PGPUB	2003/04/11 10:22
	1	("5409538").PN.	USPAT; US-PGPUB	2003/04/11 16:07
	102	427/8-10.ccls. not (430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) not (430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/14 12:48

-	10	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location) 427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) same (accelerat\$3 or decelerat\$3 or position\$3 or location) not (427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 15:36 2003/09/27 15:37
-	1	"4451507".PN.	USPAT;	2003/04/14 15:52
-	1	"5500243".PN.	USPAT;	2003/04/14 15:59
-	1	"5843527".PN.	USPAT;	2003/04/14 16:00
-	1332	430/30.ccls. not (430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 15:10
-	23	430/22,30,311,313,322,330.ccls. and ((contribut\$6 near3 degree or proportion or coefficien\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 16:29
-	1725	(430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)) not (430/22,30,311,313,322,330.ccls. and ((contribut\$6 near3 degree or proportion or coefficien\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4))) )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 14:44
-	671	(430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 14:59

	5	427/8-10 not (430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)) not (430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 15:12
	71	(substrate or wafer) near3 (defect or fault) same (nozzle or pipe or spread\$3 or flow\$3 or dispens\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 15:12
	13	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 15:36
	12	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) same (accelerat\$3 or decelerat\$3 or position\$3 or location) not (427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 15:38
	8	(427/8-10 or 438/5-18).ccls. and ((contribut\$6 near3 degree or proportion or coefficien\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/27 17:00
	16	(427/8-10 or 438/5-18).ccls. and (formula\$1 or equation) same (resist or photoresist) same thick\$4 not ((contribut\$6 near3 degree or proportion or coefficien\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/29 16:46
	51	(430/22,30 or 438/5-18).ccls. and (etch\$3 near3 (line or pattern) same (alarm\$3 or alert\$3 or warn\$3 or buzz\$3 or signal\$4 or notif\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/29 17:22
	75	semiconduct\$3 and (etch\$3 same (alarm\$3 or alert\$3 or warn\$3 or buzz\$3 or notif\$4) same (operator or human3 or manual\$3 or person\$6 or eye\$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/09/29 17:26